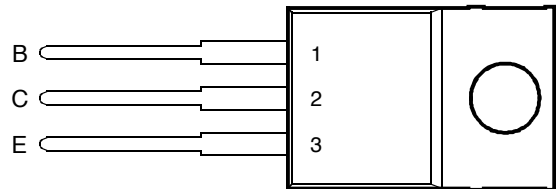


- Rugged Triple-Diffused Planar Construction
- 4 A Continuous Collector Current
- Operating Characteristics Fully Guaranteed at 100°C
- 1000 Volt Blocking Capability
- 75 W at 25°C Case Temperature

TO-220 PACKAGE
(TOP VIEW)



Pin 2 is in electrical contact with the mounting base.

MDTRACA



This series is obsolete and not recommended for new designs.

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

| RATING | | SYMBOL | VALUE | UNIT |
|---|----------|-----------|-------------|------|
| Collector-base voltage ($I_E = 0$) | TIPL760 | V_{CBO} | 850 | V |
| | TIPL760A | | 1000 | |
| Collector-emitter voltage ($V_{BE} = 0$) | TIPL760 | V_{CES} | 850 | V |
| | TIPL760A | | 1000 | |
| Collector-emitter voltage ($I_B = 0$) | TIPL760 | V_{CEO} | 400 | V |
| | TIPL760A | | 450 | |
| Emitter-base voltage | | V_{EBO} | 10 | V |
| Continuous collector current | | I_C | 4 | A |
| Peak collector current (see Note 1) | | I_{CM} | 8 | A |
| Continuous device dissipation at (or below) 25°C case temperature | | P_{tot} | 75 | W |
| Operating junction temperature range | | T_j | -65 to +150 | °C |
| Storage temperature range | | T_{stg} | -65 to +150 | °C |

NOTE 1: This value applies for $t_p \leq 10$ ms, duty cycle $\leq 2\%$.

PRODUCT INFORMATION

AUGUST 1978 - REVISED SEPTEMBER 2002
Specifications are subject to change without notice.

electrical characteristics at 25°C case temperature (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | | | MIN | TYP | MAX | UNIT |
|--|--------------------------|----------------------|---------------------------|---------------------|------------|-----|---------------|
| $V_{CE(sus)}$ Collector-emitter sustaining voltage | $I_C = 10\text{ mA}$ | $L = 25\text{ mH}$ | (see Note 2) | TIPL760 TIPL760A | 400 450 | | V |
| I_{CES} Collector-emitter cut-off current | $V_{CE} = 850\text{ V}$ | $V_{BE} = 0$ | | TIPL760 | | 50 | μA |
| | $V_{CE} = 1000\text{ V}$ | $V_{BE} = 0$ | | TIPL760A | | 50 | |
| | $V_{CE} = 850\text{ V}$ | $V_{BE} = 0$ | $T_C = 100^\circ\text{C}$ | TIPL760 | | 200 | |
| | $V_{CE} = 1000\text{ V}$ | $V_{BE} = 0$ | $T_C = 100^\circ\text{C}$ | TIPL760A | | 200 | |
| I_{CEO} Collector cut-off current | $V_{CE} = 400\text{ V}$ | $I_B = 0$ | | TIPL760 | | 50 | μA |
| | $V_{CE} = 450\text{ V}$ | $I_B = 0$ | | TIPL760A | | 50 | |
| I_{EBO} Emitter cut-off current | $V_{EB} = 10\text{ V}$ | $I_C = 0$ | | | | 1 | mA |
| h_{FE} Forward current transfer ratio | $V_{CE} = 5\text{ V}$ | $I_C = 0.5\text{ A}$ | (see Notes 3 and 4) | | 20 | 60 | |
| $V_{CE(sat)}$ Collector-emitter saturation voltage | $I_B = 0.5\text{ A}$ | $I_C = 2.5\text{ A}$ | | | | 1.0 | V |
| | $I_B = 0.8\text{ A}$ | $I_C = 4\text{ A}$ | (see Notes 3 and 4) | | | 2.5 | |
| | $I_B = 0.8\text{ A}$ | $I_C = 4\text{ A}$ | $T_C = 100^\circ\text{C}$ | | | 5.0 | |
| $V_{BE(sat)}$ Base-emitter saturation voltage | $I_B = 0.5\text{ A}$ | $I_C = 2.5\text{ A}$ | | | | 1.2 | V |
| | $I_B = 0.8\text{ A}$ | $I_C = 4\text{ A}$ | (see Notes 3 and 4) | | | 1.4 | |
| | $I_B = 0.8\text{ A}$ | $I_C = 4\text{ A}$ | $T_C = 100^\circ\text{C}$ | | | 1.3 | |
| f_t Current gain bandwidth product | $V_{CE} = 10\text{ V}$ | $I_C = 0.5\text{ A}$ | $f = 1\text{ MHz}$ | | 12 | | MHz |
| C_{ob} Output capacitance | $V_{CB} = 20\text{ V}$ | $I_E = 0$ | $f = 0.1\text{ MHz}$ | | 110 | | pF |

NOTES: 2. Inductive loop switching measurement.

3. These parameters must be measured using pulse techniques, $t_p = 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

4. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

| PARAMETER | MIN | TYP | MAX | UNIT |
|---|-----|-----|------|--------------------|
| $R_{\theta JC}$ Junction to case thermal resistance | | | 1.56 | $^\circ\text{C/W}$ |

inductive-load-switching characteristics at 25°C case temperature (unless otherwise noted)

| PARAMETER | TEST CONDITIONS † | | | MIN | TYP | MAX | UNIT |
|-------------------------------|---|----------------------------|-----------------------|-----|---------------------------|-----|---------------|
| t_{sv} Voltage storage time | $I_C = 4\text{ A}$ $V_{BE(off)} = -5\text{ V}$ | $I_{B(on)} = 0.8\text{ A}$ | (see Figures 1 and 2) | | | 2.5 | μs |
| t_{rv} Voltage rise time | | | | | | 300 | ns |
| t_{fi} Current fall time | | | | | | 250 | ns |
| t_{ti} Current tail time | | | | | | 150 | ns |
| t_{xo} Cross over time | | | | | | 400 | ns |
| t_{sv} Voltage storage time | $I_C = 4\text{ A}$ $V_{BE(off)} = -5\text{ V}$ | $I_{B(on)} = 0.8\text{ A}$ | (see Figures 1 and 2) | | | 3 | μs |
| t_{rv} Voltage rise time | | | | | | 500 | ns |
| t_{fi} Current fall time | | | | | | 250 | ns |
| t_{ti} Current tail time | | | | | $T_C = 100^\circ\text{C}$ | 150 | ns |
| t_{xo} Cross over time | | | | | | 750 | ns |

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

PARAMETER MEASUREMENT INFORMATION

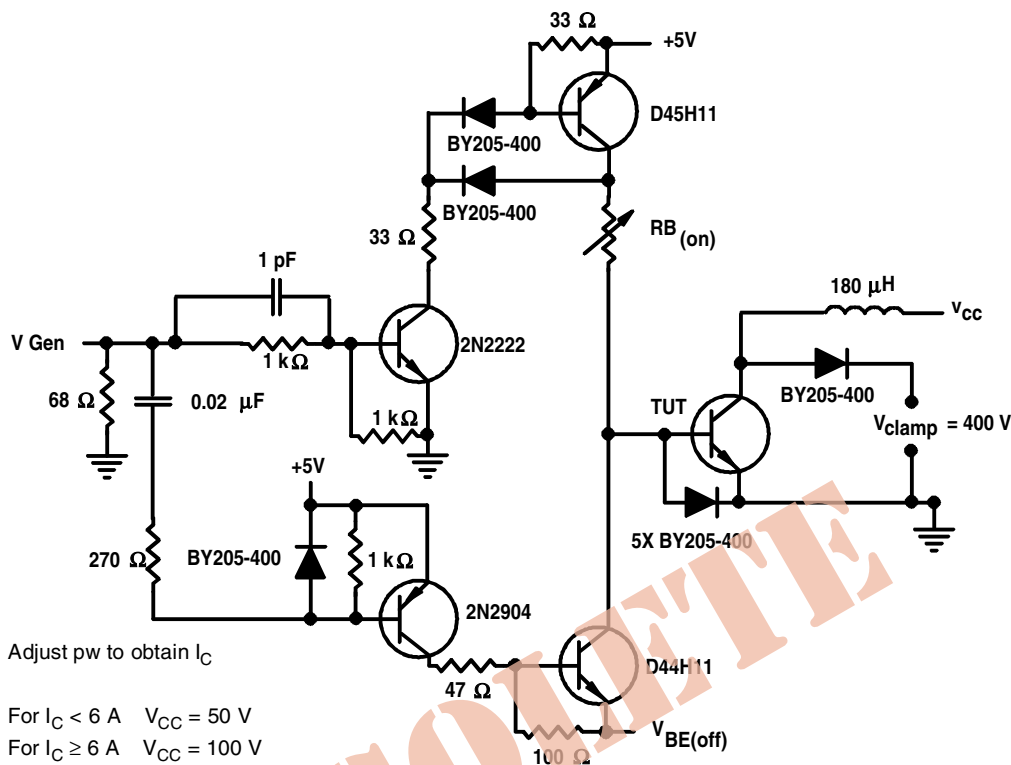
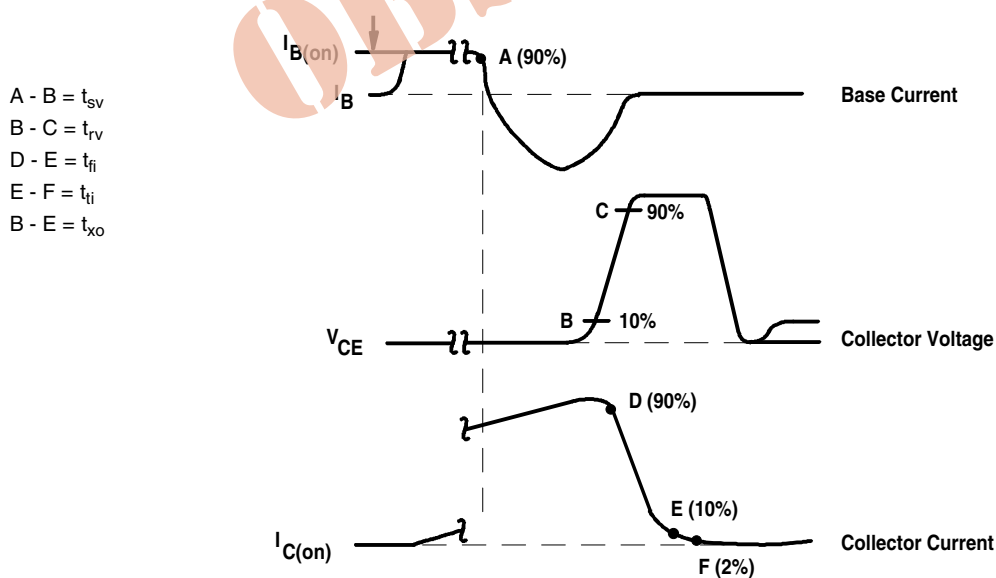


Figure 1. Inductive-Load Switching Test Circuit



NOTES: A. Waveforms are monitored on an oscilloscope with the following characteristics: $t_r < 15 \text{ ns}$, $R_{in} > 10 \Omega$, $C_{in} < 11.5 \text{ pF}$.
 B. Resistors must be noninductive types.

Figure 2. Inductive-Load Switching Waveforms

PRODUCT INFORMATION

AUGUST 1978 - REVISED SEPTEMBER 2002
 Specifications are subject to change without notice.

TYPICAL CHARACTERISTICS

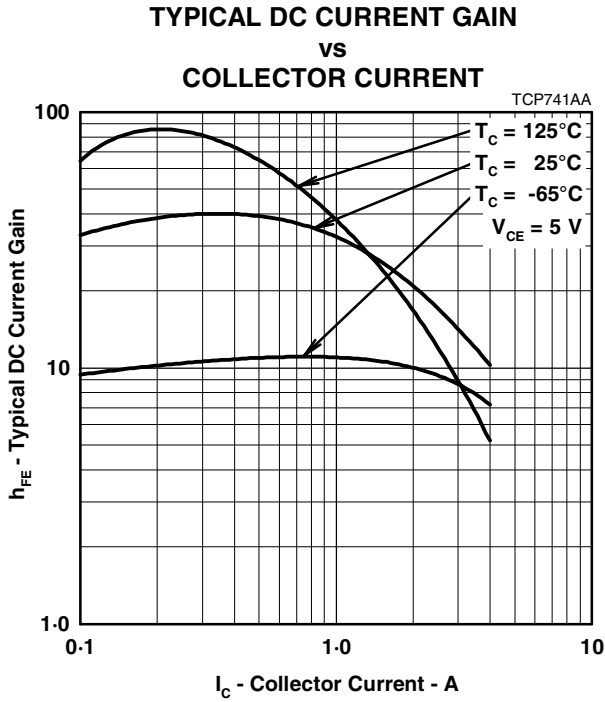


Figure 3.

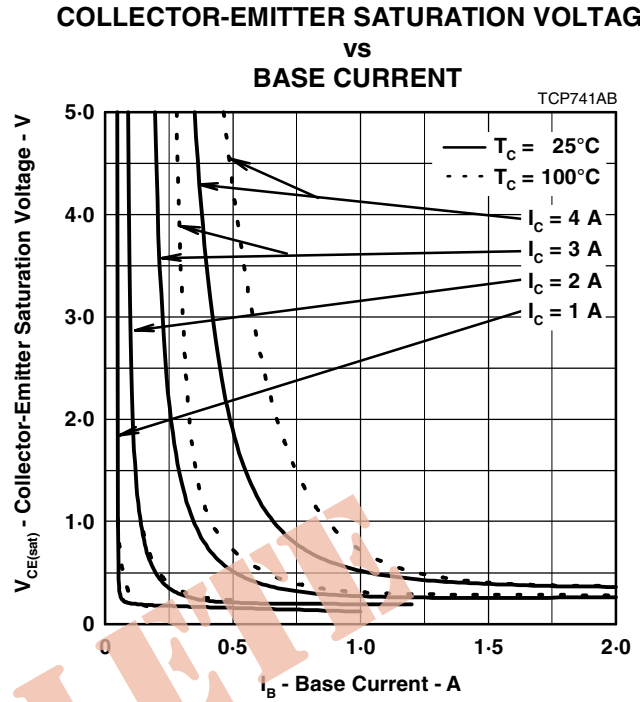


Figure 4.

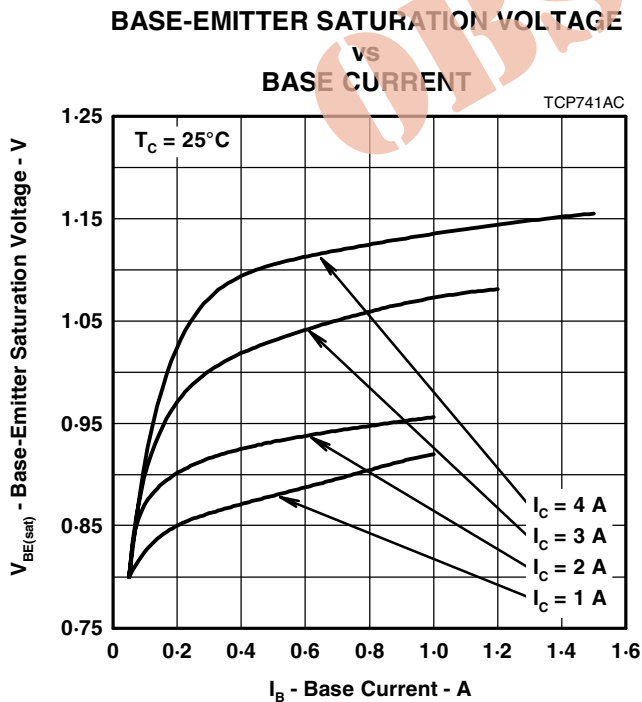


Figure 5.

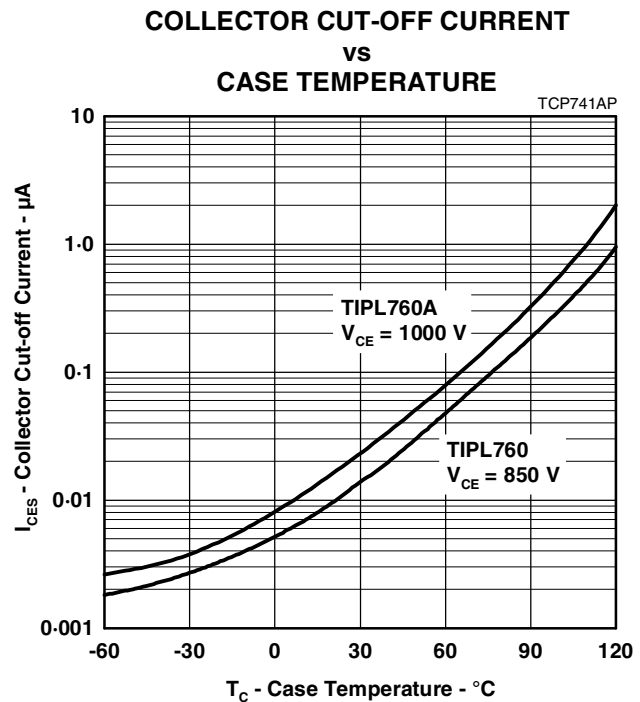


Figure 6.

PRODUCT INFORMATION

AUGUST 1978 - REVISED SEPTEMBER 2002
Specifications are subject to change without notice.

MAXIMUM SAFE OPERATING REGIONS

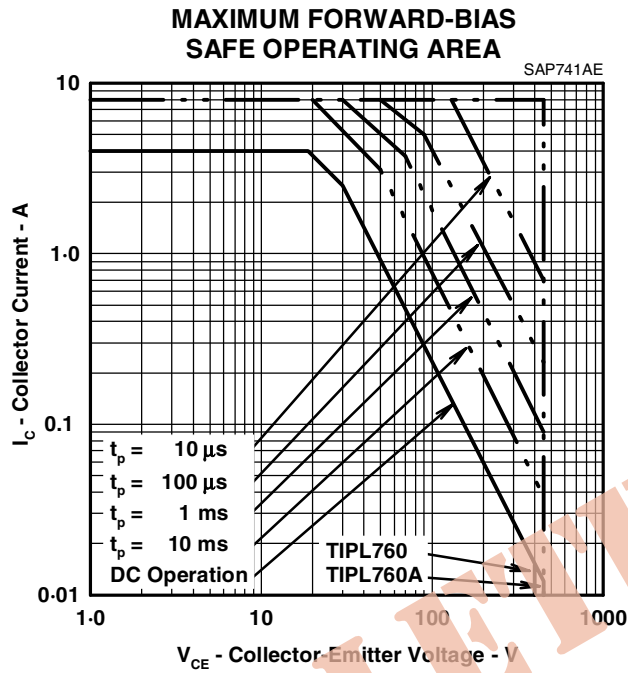


Figure 7.

THERMAL INFORMATION

**THERMAL RESPONSE JUNCTION TO CASE
VS
POWER PULSE DURATION**

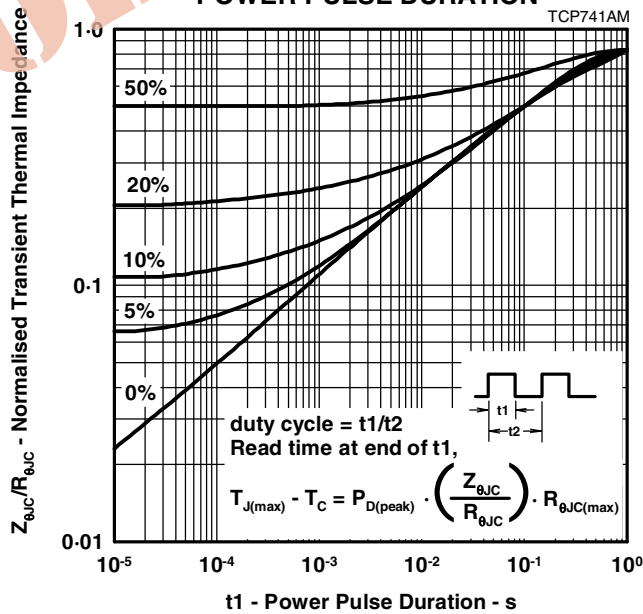


Figure 8.

PRODUCT INFORMATION

AUGUST 1978 - REVISED SEPTEMBER 2002
Specifications are subject to change without notice.